L Number	Hits	Search Text	DB	Time stamp
1	167931	control$2 near2 valve	USPAT; US-PGPUB	2003/12/31 13:23
2	496	charge near2 surface near2 (sample mask wafer workpiece)	USPAT; US-PGPUB	2003/12/31 13:25
3	18	(control$2 near2 valve) and (charge near2 surface near2 (sample mask wafer workpiece))	USPAT; US-PGPUB	2003/12/31 13:25
4	20733	charge near2 (monitor sens$3 detect$3)	USPAT; US-PGPUB	2003/12/31 13:25
5	1923	(charge near2 (monitor sens$3 detect$3)) and rising	USPAT; US-PGPUB	2003/12/31 13:25
6	797	((charge near2 (monitor sens$3 detect$3)) and rising) and (sample mask wafer workpiece)	USPAT; US-PGPUB	2003/12/31 13:28
7	28	(control$2 near2 valve) and (((charge near2 (monitor sens$3 detect$3)) and rising) and (sample mask wafer workpiece))	USPAT; US-PGPUB	2003/12/31 13:26
8	117	((charge near2 (monitor sens$3 detect$3)) and rising) and wafer	USPAT; US-PGPUB	2003/12/31 13:34
9	24306	wafer near2 process	USPAT; US-PGPUB	2003/12/31 13:34
10	289	(charge near2 (monitor sens$3 detect$3)) and (wafer near2 process)	USPAT; US-PGPUB	2003/12/31 13:43
11	18	(control$2 near2 valve) and ((charge near2 (monitor sens$3 detect$3)) and (wafer near2 process))	USPAT; US-PGPUB	2003/12/31 13:34
12	217	ESD and (wafer near2 process)	USPAT; US-PGPUB	2003/12/31 13:50
13	186	(determin$2 compar$2) near2 charge and (wafer near2 process)	USPAT; US-PGPUB	2003/12/31 13:52
14	3	(control$2 near2 valve) and ((determin$2 compar$2) near2 charge and (wafer near2 process))	USPAT; US-PGPUB	2003/12/31 13:51
15	309	(determin$2 compar$2 measur$2) near2 charge and (wafer near2 process)	USPAT; US-PGPUB	2003/12/31 14:15
16	107	((determin$2 compar$2 measur$2) near2 charge and (wafer near2 process)) and (valve rising)	USPAT; US-PGPUB	2003/12/31 13:53
17	182	(determin$2 compar$2 measur$2) near2 charge and drying near2 process	USPAT; US-PGPUB	2003/12/31 14:38
18	14	((determin$2 compar$2 measur$2) near2 charge and drying near2 process) and wafer	USPAT; US-PGPUB	2003/12/31 14:23
19	2210	exceed$2 near2 charge	USPAT; US-PGPUB	2003/12/31 14:23
20	11	(wafer near2 process) and (exceed$2 near2 charge)	USPAT; US-PGPUB	2003/12/31 14:29
21	151	drying and (exceed$2 near2 charge)	USPAT; US-PGPUB	2003/12/31 14:30
22	2	(drying and (exceed$2 near2 charge)) and wafer	USPAT; US-PGPUB	2003/12/31 14:30
23	0	spin near2 drying and (exceed$2 near2 charge)	USPAT; US-PGPUB	2003/12/31 14:30
24	64	spin and (exceed$2 near2 charge)	USPAT; US-PGPUB	2003/12/31 14:30
25	5	(spin and (exceed$2 near2 charge)) and wafer	USPAT; US-PGPUB	2003/12/31 14:31
27	0	(exceed$2 near2 charge) and (sensor near2 arm and wafer near2 process)	USPAT; US-PGPUB	2003/12/31 14:32
26	133	sensor near2 arm and wafer near2 process	USPAT; US-PGPUB	2003/12/31 14:35
28	125	dispens$2 and (exceed$2 near2 charge)	USPAT; US-PGPUB	2003/12/31 14:35
29	4	(dispens$2 and (exceed$2 near2 charge)) and wafer	USPAT; US-PGPUB	2003/12/31 14:35
30	91	(determin$2 compar$2) near2 charge and drying near2 process	USPAT; US-PGPUB	2003/12/31 14:38